

SAIYO	No.268J	<h1 style="margin: 0;">2SB598/2SD545</h1> <p style="margin: 0;">PNP/NPN Epitaxial Planar Silicon Transistors</p> <p style="margin: 0;">AF Power Amp, Converter, Electronic Governor Applications</p>
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The 2SB598/2SD545 are complementary pair transistors that are packaged in small packages and are large in current capacity and excellent in saturation characteristic and h_{FE} linearity. In addition to the above application areas, they are also suited for use in desk-top calculator power supplies, relay drivers.

Absolute Maximum Ratings at $T_a = 25^\circ\text{C}$

		unit
Collector to Base Voltage	V_{CB0}	(-)25 V
Collector to Emitter Voltage	V_{CEO}	(-)25 V
Emitter to Base Voltage	V_{EBO}	(-)5 V
Collector Current	I_C	(-)1.0 A
Collector Current(Pulse)	I_{CP}	(-)1.5 A
Collector Dissipation	P_C	600 mW
Junction Temperature	T_j	150 $^\circ\text{C}$
Storage Temperature	T_{stg}	- 55 to + 150 $^\circ\text{C}$

Electrical Characteristics at $T_a = 25^\circ\text{C}$

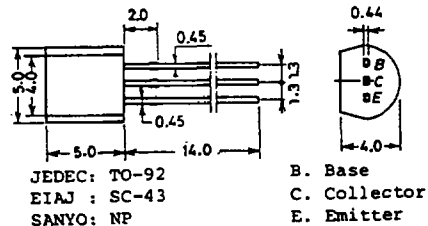
			min	typ	max	unit
Collector Cutoff Current	I_{CBO}	$V_{CB} = (-)20\text{V}, I_E = 0$			(-)1.0	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB} = (-)4\text{V}, I_C = 0$			(-)1.0	μA
DC Current Gain	$h_{FE}(1)$	$V_{CE} = (-)2\text{V}, I_C = (-)50\text{mA}$	60※		560※	
	$h_{FE}(2)$	$V_{CE} = (-)2\text{V}, I_C = (-)1\text{A}(\text{pulse})$	30			
Gain-Bandwidth Product	f_T	$V_{CE} = (-)10\text{V}, I_C = (-)50\text{mA}$		180		MHz
Output Capacitance	c_{ob}	$V_{CB} = (-)10\text{V}, f = 1\text{MHz}$		(25)15		pF
C-E Saturation Voltage	$V_{CE(sat)}$	$I_C = (-)500\text{mA}, I_B = (-)50\text{mA}$		0.1	0.3	V
				(-0.15)	(-0.5)	V
B-E Saturation Voltage	$V_{BE(sat)}$	$I_C = (-)500\text{mA}, I_B = (-)50\text{mA}$		(-)0.85	(-)1.2	V
C-B Breakdown Voltage	$V_{(BR)CBO}$	$I_C = (-)10\mu\text{A}, I_E = 0$	(-)25			V
C-E Breakdown Voltage	$V_{(BR)CEO}$	$I_C = (-)1\text{mA}, R_{BE} = \infty$	(-)25			V
E-B Breakdown Voltage	$V_{(BR)EBO}$	$I_E = (-)10\mu\text{A}, I_C = 0$	(-)5			V

※ : The 2SB598/2SD545 are classified by 50mA h_{FE} as follows :

60 D 120	100 E 200	160 F 320	280 G 560
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h_{FE} rank : D,E,F,G

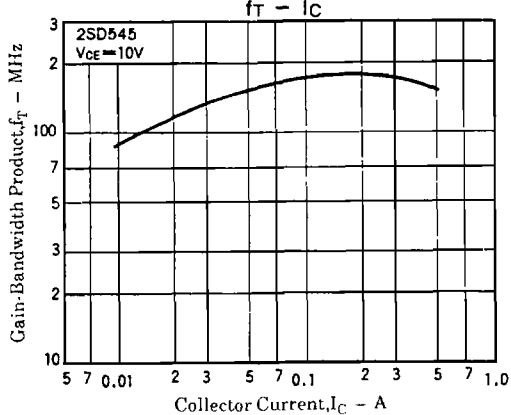
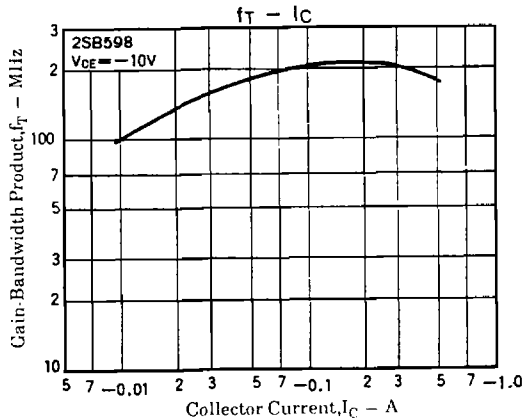
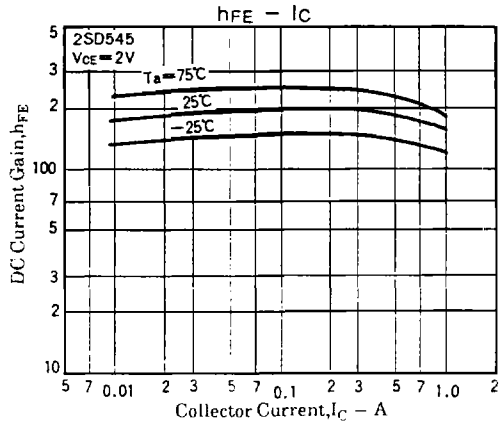
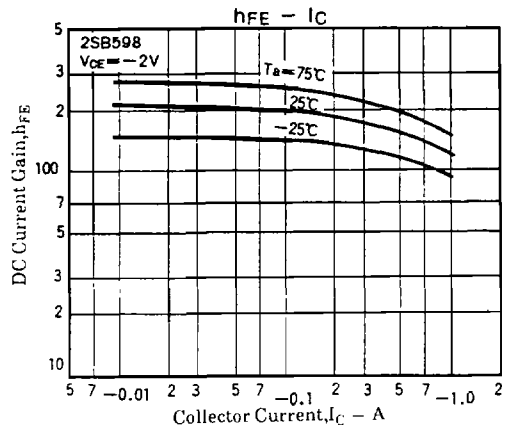
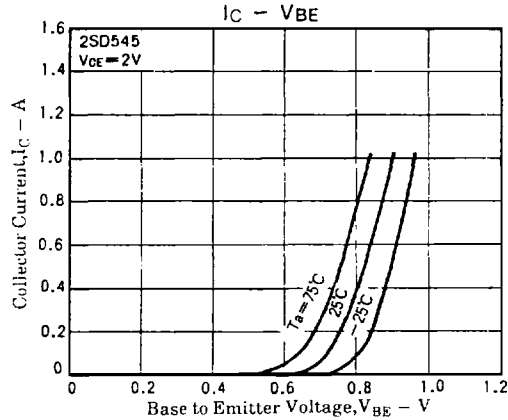
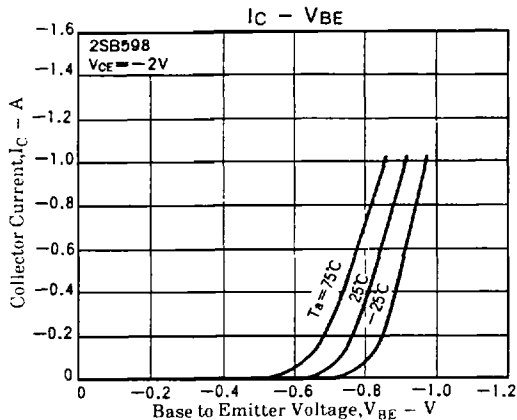
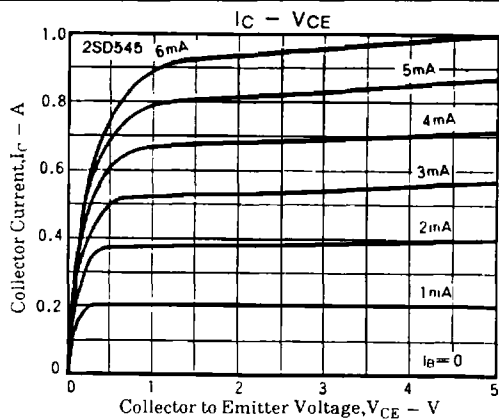
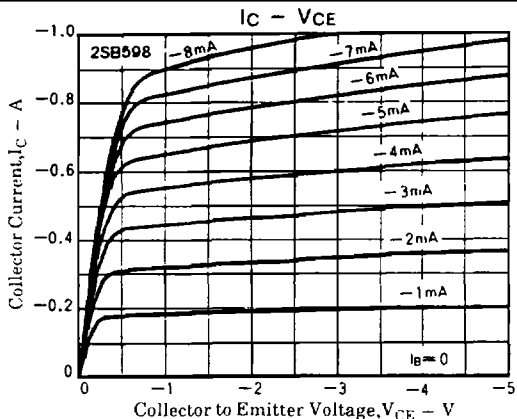
Case Outline 2003A
(unit : mm)



Specifications and information herein are subject to change without notice.

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2SB598/2SD545

